

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended) A method of manufacturing a lithography mask blank on a ~~transparent~~ glass substrate, comprising the steps of:  
  
depositing, on the ~~transparent~~ glass substrate, at least one light absorption film which has a property of absorbing a laser of a predetermined wavelength transmitted through the glass substrate; and  
  
irradiating a laser beam of the predetermined wavelength onto the light absorption film to selectively heat the light absorption film and to thereby alleviate its internal stress.
2. (original) A method as claimed in claim 1, wherein the mask blank is a phase shift mask blank while the light absorption film is formed by a translucent film which serves as a phase shift film of the phase shift mask blank so as to attenuate exposure light of predetermined intensity.
3. (original) A method as claimed in claim 1, wherein the light absorption film is an opaque film.
4. (original) A method as claimed in claim 1, wherein the laser beam is irradiated onto the mask blank so that the transparent glass substrate with the light absorption film has flatness not greater than 0.5 micron meter.
5. (original) A lithography mask blank manufactured by the method claimed in claim 1.

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6. (original) A lithography mask manufactured by the use of the mask blank claimed in claim 5.

7. (new): A method of manufacturing a lithography mask as claimed in claim 1 wherein the step of irradiating comprises heating the light absorption film for a period on the order of several tens of nanoseconds.

8. (new): A method of manufacturing a lithography mask as claimed in claim 1 wherein the step of irradiating comprises heating the light absorption film to a temperature of at least 1000°C.

9. (new): A method of manufacturing a lithography mask as claimed in claim 1 wherein the light absorption film comprises a light translucent film.

10. (new): A method of manufacturing a lithography mask as claimed in claim 1 wherein the light absorption film comprises MoSiN.

11. (new) A lithography mask as recited in claim 6 wherein mask blank is a phase shift mask blank of a half tone type.